

**In the Claims:**

Cancel non-elected claims 37-45.

Amend claims the as follows:

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1. (Amended) A method for depositing a platinum group metal on a substrate, comprising the steps of:

B1  
depositing said platinum group metal onto a substrate in a CVD deposition chamber in the presence of both oxygen and nitrous oxide at a predetermined temperature and at a pressure of from about 10 to about 1000 Torr.

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6. (Amended) A method for depositing a platinum group metal on a substrate, comprising the steps of:

introducing a substrate into a CVD deposition chamber;

B2  
bubbling a gas over an organic platinum based metal precursor;

introducing said gas and said organic platinum based metal precursor to said CVD deposition chamber;

introducing oxygen to said CVD deposition chamber;

introducing nitrous oxide to said deposition chamber; and

depositing said platinum group metal onto said substrate in said CVD deposition chamber at a predetermined temperature and at a pressure of from about 10 to about 1000 Torr.

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B3  
8. (Amended) The method according to claim 6, wherein said organic platinum based metal precursor is selected from the group consisting of cyclopentadienyl trimethylplatinum (IV) and methylcyclopentadienyl trimethylplatinum [CH<sub>3</sub>(C<sub>5</sub>H<sub>5</sub>)Pt(CH<sub>3</sub>)<sub>3</sub>].

B3299  
9. (Amended) The method according to claim 8, wherein said organic platinum based metal precursor is methylcyclopentadienyl trimethylplatinum  $[\text{CH}_3(\text{C}_5\text{H}_5)\text{Pt}(\text{CH}_3)_3]$ .

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B4  
20. (Amended) The method according to claim 6, wherein said substrate is selected from the group consisting of [BPSG,] [Si] silicon, TiN, Ti, oxides, [PSG,]  $\text{Si}_3\text{N}_2$ , [polysilicon] and silicide.

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21. (Amended) The method according to claim 20, wherein said substrate is selected from the group consisting of [BPSG] borophosphosilicate glass and [Si] silicon.

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25. (Amended) A method for depositing platinum onto a substrate, comprising the steps of:

introducing a substrate into a CVD deposition chamber;

bubbling a non-reactive gas over an organic platinum precursor selected from the group consisting of cyclopentadienyl trimethylplatinum (IV) and methylcyclopentadienyl trimethylplatinum  $[\text{CH}_3(\text{C}_5\text{H}_5)\text{Pt}(\text{CH}_3)_3]$ ;

B5  
introducing said non-reactive gas and said organic platinum precursor to said CVD deposition chamber;

introducing a 50/50 mixture by volume of oxygen and nitrous oxide to said CVD deposition chamber;

depositing said platinum group metal onto said substrate in said CVD deposition chamber at a temperature of from about 200 to about 600 °C and pressure of from about [1] 10 to about 1000 Torr to form a continuous, substantially uniform film on said substrate [with good step coverage].

26. (Amended) The method according to claim 25, wherein said organic platinum precursor is methylcyclopentadienyl trimethylplatinum  $[\text{CH}_3(\text{C}_5\text{H}_5)\text{Pt}(\text{CH}_3)_3]$ .

B5 and 27. (Amended) The method according to claim 25, wherein said substrate is selected from the group consisting of [BPSG,] [Si] silicon, TiN, Ti, oxides, [PSG,] Si<sub>3</sub>N<sub>2</sub>, [polysilicon] and silicide.

28. (Amended) The method according to claim 27, wherein said substrate is selected from the group consisting of [BPSG] borophosphosilicate glass and [Si] silicon.

[Cancel claims 5 and 11.]

[--Please add the following new claims 46-55:]

46. The method according to claim 1, wherein said pressure is from about 10 to about 50 Torr.

47. The method according to claim 1, wherein said pressure is from about 15 to about 30 Torr.

48. The method according to claim 6, wherein said pressure is from about 10 to about 50 Torr.

B6 49. The method according to claim 6, wherein said pressure is from about 15 to about 30 Torr.

50. The method according to claim 20, wherein said oxides are selected from the group consisting of borophosphosilicates and phosphosilicates.

51. The method according to claim 21, wherein said substrate is formed of polysilicon.

52. The method according to claim 25, wherein said pressure is from about 10 to about 50 Torr.

53. The method according to claim 25, wherein said pressure is from about 15 to about 30 Torr.--

54. The method according to claim 28, wherein said oxides are selected from the group consisting of borophosphosilicates and phosphosilicates.

55. The method according to claim 21, wherein said substrate is formed of polysilicon.

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### REMARKS

Non-elected Claim 37-45 have been cancelled. Claims 5 and 11 have been cancelled. New claims 46-55 have been added. Claims 1, 6, 8-9, 20-21 and 25-28 have been amended. Applicant reserves the right to pursue the original claims and other claims in this application and in other applications. Claims 1-4, 6-10, 12-36 and 46-55 are pending in this application.

The Office Action states that formal drawings will be required when the application is allowed. Applicants respectfully submit that formal drawings be deferred until receipt of a Notice of Allowance.

Claims 8,9, 20-21 and 25-28 stand objected to for informalities. These claims have been amended herein to remove any perceived informalities.

Claims 20 and 25-36 stand rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claims 20, 25 and 27 have been amended to correct any deficiencies noted in accordance with the Examiner's suggestions. Applicant respectfully submits that all pending claims are now in full compliance with 35 U.S.C. § 112, second paragraph.

Claims 1-36 stand rejected under 35 U.S.C. § 103 (a) as being unpatentable over Baum et al. (U.S. Patent No. 5,783,716). The present invention relates to a method